Contribution ID: **136** Type: **Talk**

Evolution of Dislocations in GaAs Wafers Investigated by Means of X-ray Diffraction Imaging

Wednesday, 16 March 2022 09:20 (20 minutes)

Gallium arsenide is one of the most important materials for optoelectronic. During manufacturing, the presence of like dislocations may influence the fabrication yield and the performance of the devices. This study provides a deeper understanding of dislocation generation and development in GaAs wafers with mechanical surface damage exposed to thermally induced stress investigated by X-ray diffraction imaging methods.

Primary author: KABUKCUOGLU, Merve (Ms)

Co-authors: Dr HÄNSCHKE, Daniel (KIT); Dr HAMANN, Elias (KIT); Mr HAAGA, Simon (KIT); Mr BODE, Simon (KIT); BAUMBACH, Tilo (Karlsruher Institut für Technologie, Hermann-von-Helmholtzplatz, 1 76344 Eggenstein-Leopoldshafen); Prof. DANILEWSKY, Andreas (Uni Freiburg)

Presenter: KABUKCUOGLU, Merve (Ms)

Session Classification: Crystallization and Crystal Growth Processes

Track Classification: Main conference: Crystallization, Crystal Growth Processes, Synthesis